

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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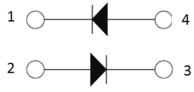




SiC SBD Anti-Parallel

Power Module





Anti-Parallel

$V_{RRM} = 1200V$ $I_{DAV} = 45A @T_{C} = 125^{0}C$

Features

- · SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on V_F
- Low stray inductance
- High junction temperature operation

Applications

- Supplies for DC power equipment
- Rectifier for induction heating
- Welding equipment
- High temperature and rectifiers



Benefits

- Outstanding performance at high frequency operation
- Low losses and Low EMI noises
- Very rugged and easy mount
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive Tc of VF
- RoHS Compliant

Absolute Maximum Ratings (T_i=25°C unless otherwise specified)

Parameters	Symbol	Conditions	Specifications	Units
Maximum Reverse Voltage	V_{RRM}		1200	V
Average Forward Current (per SBD)	I _{DAV}	$T_{\rm C} = 25{}^{\rm 0}{\rm C}$	121	Α
		$T_{\rm C} = 150{}^{\rm 0}{\rm C}$	45	Α
Non-repetitive Forward Surge Current	I _{FSM}	$t=8.3 \text{ ms}, T_{C} = 150 {}^{\circ}\text{C}$	225	Α
		T=10 μ s, T _C = 25 $^{\circ}$ C	900	Α
Operating Junction Temperature	T _j		-55 ~ 175	°C
Storage Temperature	T _{STG}		-55 ~ 1 50	°C

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Electrical Characteristics (T_j=25°C unless otherwise specified)

Parameters	Symbol	Conditions	Min	Тур	Max	Units
Maximum peak repetitive reverse voltage	V _{RRM}		1200			V
Maximum Reverse Leakage Current	I _{RM}	$V_R = 1200V, T_j = 25^{\circ}C$		13	300	μΑ
		$V_R = 1200V, T_j = 150$ °C		1818		μΑ
Diode Forward Voltage	V _F	$I_F = 45A, T_j = 25$ °C		1.5	1.7	V
		$I_F = 45A, T_j = 150$ °C		2.3		V
Total Capacitive Charge	Q _C	VR=1200 V, IF <if,max< td=""><td></td><td>156</td><td></td><td>nC</td></if,max<>		156		nC
Switching Time	t _C	$dI_F/dt = 200 A/\mu s$, $T_j = 175 {}^{0}C$			10	ns
Total Capacitance	С	V _R = 1V, f = 1 MHz		2700		pF
		V _R = 600V, f = 1 MHz		156		pF
		V _R = 1200V, f = 1 MHz		126		pF

Thermal and Package Characteristics (T_j=25°C unless otherwise specified)

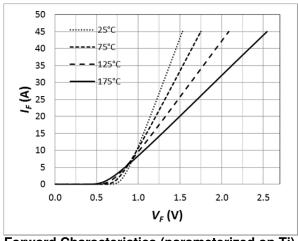
Parameters	Symbol	Conditions	Min	Тур	Max	Units
Junction to Case Thermal Resistance	R _{THJC}	Per Diode			022	°C /W
Junction to Ambient Thermal Resistance	R _{THJA}	Per Diode			20	°C /W
Mounting Torque	M _d				1.5	N-m
Terminal Connection Torque	M _{dt}		1.3		1.5	N-m
Package Weight	W _t			32		g
Isolation Voltage	V _{ISOL}	I _{ISOL} < 1mA, 50/60Hz, t=1 min	2500	V		

Product Number and Descriptions

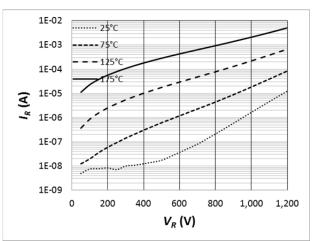
Part Number	Rating	Pin 1	Pin 2	Pin 3	Pin 4
GHXS045A120S-D4	1200V, 45A	Cathode 1	Anode 2	Cathode 2	Anode 1

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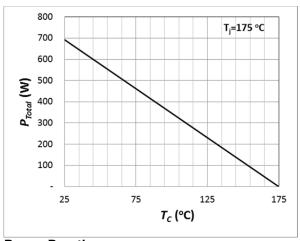




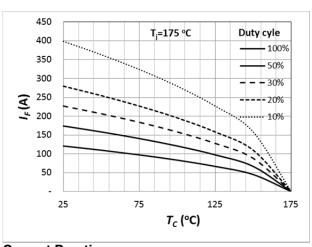
Forward Characteristics (parameterized on Tj)



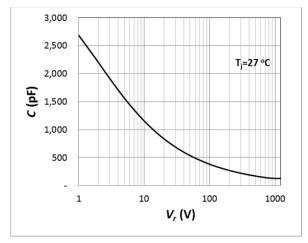
Reverse Characteristics (parameterized on Tj)



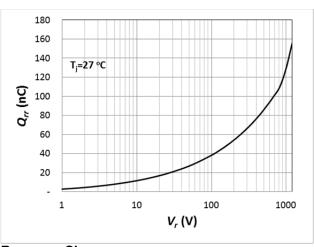
Power Derating



Current Derating

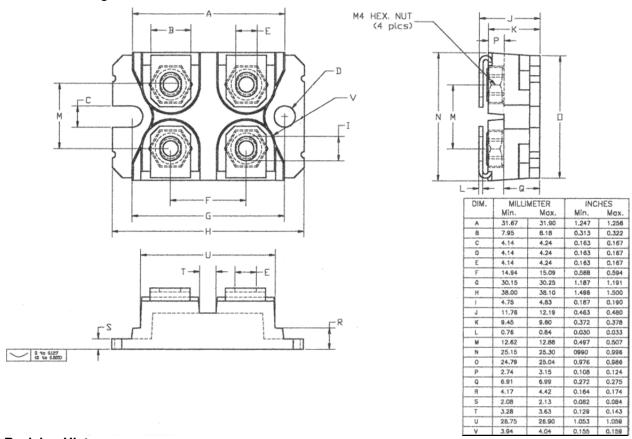


Capacitance Curve



Recovery Charge

SOT-227 Package Outline



Revision History

Date	Revision	Notes
9/6/2013	1.0	Initial release
6/4/2014	1.1	Add the part number, pin assignment table.
12/29/2014	1.2	Change the pin assignment table (swapped anode and cathode)

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Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.gptechgroup.com.

REACh Compliance

REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemi- cal Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at GPTG Headquarters in Lake Forest, California to insure you get the most up-to-date REACh SVHC Declaration.

REACh banned substance information (REACh Article 67) is also available upon request.

- This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control.
- To obtain additional technical information or to place an order for this product, please contact
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